45. (Twice Amended) The capacitors of claim 44 wherein each comprises:

a stem; and

in cross-section, at least two laterally opposed fins interconnected with and projecting laterally from the stem, the stem having a minimum width which is less than the minimum photolithographic feature dimension [with which the capacitors are fabricated].

New Claims

~~46.~~ 51. The capacitors of claim 44, wherein the lower plates are formed from conductive polysilicon.

~~47.~~ 52. The capacitors of claim 45, wherein the stem and fins are formed from conductive polysilicon.

~~48.~~ 53. The capacitors of claim 45, wherein the pair of stacked capacitors are coated with a capacitor dielectric layer.

54
~~49~~. A pair of adjacent stacked capacitors fabricated relative to a semiconductor substrate, the adjacent stacked capacitors respectively including a lower plate having a minimum lateral spacing from one another which is less than a minimum photolithographic feature dimension, each lower plate comprising a stem and, in cross-section, at least two laterally opposed fins interconnected with and projecting laterally from the stem.

D3 cont

55
~~50~~. The capacitors of claim 54 ~~49~~, wherein the minimum photolithographic feature dimension is one with which the capacitors are fabricated.

56
~~51~~. The capacitors of claim 54 ~~49~~ wherein the stem includes a minimum width which is less than the minimum photolithographic feature dimension.

57
~~52~~. The capacitors of claim 56 ~~51~~, wherein the minimum photolithographic feature dimension is one with which the capacitors are fabricated.

58
~~53~~. The capacitors of claim 56 ~~49~~, wherein the lower plates are formed from conductive polysilicon.

59 56
54. The capacitors of claim 49, wherein the stem and fins are formed from conductive polysilicon.

60 56
55. The capacitors of claim 49, wherein the pair of stacked capacitors are coated with a capacitor dielectric layer.

61
56. A pair of adjacent stacked capacitors fabricated relative to a semiconductor substrate, the adjacent stacked capacitors respectively including a finned lower plate having a minimum lateral spacing from one another which is less than a minimum photolithographic feature dimension.

62 61
57. The capacitors of claim 56 wherein each comprises:

a stem; and

in cross-section, at least two laterally opposed fins interconnected with and projecting laterally from the stem, the stem having a minimum width which is less than the minimum photolithographic feature dimension.

63 61
58. The capacitors of claim 56, wherein the minimum photolithographic feature dimension is one with which the capacitors are fabricated.

64 62
~~59~~. The capacitors of claim ~~51~~ wherein the stem includes a minimum width which is less than the minimum photolithographic feature dimension.

65 64
~~60~~. The capacitors of claim ~~59~~, wherein the minimum photolithographic feature dimension is one with which the capacitors are fabricated.

D3 cont

66 62
~~61~~. The capacitors of claim ~~56~~, wherein the lower plates are formed from conductive polysilicon.

67 62
~~62~~. The capacitors of claim ~~57~~, wherein the stem and fins are formed from conductive polysilicon.

67 62
~~63~~. The capacitors of claim ~~56~~, wherein the pair of stacked capacitors are coated with a capacitor dielectric layer.